NANOPULBERI DE SiO₂-TiO₂ sau SiO₂-TiO₂-Al₂O₃ DOPATE CU ERBIU PREPARATE PRIN METODA SOL-GEL ERBIUM DOPED SiO₂-TiO₂ OR SiO₂-TiO₂-Al₂O₃ NANOPOWDERS PREPARED BY SOL-GEL METHOD

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The Er3+ doped silica-titania or silica-titaniaalumina nanopowders were prepared by sol-gel method that represents one of the most flexible and convenient way to prepare oxide films and nanopowders. The selected molar compositions were un-doped and 0.5%Er₂O₃ doped 90%SiO₂-10%TiO₂ and 85%SiO₂-10%TiO₂-5%Al₂O₃ systems. Similar compositions were previously used for obtaining films for waveguides applications but the mechanism of the phase formation by thermal treatment of the corresponding gels was not previously approached. The gels obtained by gelation of the solutions were analyzed by thermogravimetric thermodifferential and analysis (DTA/TGA) in order to determine their thermal behavior and by IR spectroscopy (FT-IR) and Scanning Electron Microscopy (SEM) to evaluate their structure and morphology. Based on the results obtained, the gels were thermally treated at 500°C and 900°C. The thermally treated powders were characterized by SEM, FT-IR, X-ray diffraction (XRD) and photoluminescence (PL). The significant influence of the Er³⁺ on the phase formation was established in both studied systems.

Keywords: sol-gel method, erbium, nanopowders. phase formation

1. Introduction

The Er3+ doped silica-titania or silicatitania-alumina nanopowders were prepared by solgel method that represents one of the most flexible and convenient way to prepare oxide films and nanopowders. Lanthanide luminescent ion (Ln³⁺)doped inorganic materials have become an important topic of research in nanoscience and nanotechnology [1]. The optical properties of lanthanide ion-doped silicate systems are of great interest for fundamental studies and technological applications in optical devices, such as lasers, fiber amplifiers, and waveguides. Therefore, a detailed understanding of the local structure and bonding of dopant cations is important for optical device engineering [2]. The SiO₂-TiO₂ binary system is commonly studied and can be obtained using different oxide combinations, synthesis processes,

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Nanopulberile de silice-dioxid de titan sau silice dioxid de titan-alumină dopate cu Er3+ au fost preparate prin metoda sol-gel care reprezintă una dintre cele mai flexibile și convenabile metode de preparare ale filmelor și nanopulberilor oxidice. Compozițiile moleculare selectate au fost cele din sistemele 90%SiO2-10%TiO2 și 85%SiO2--10%TiO₂-5%Al₂O₃ nedopate și dopate cu 0,5% Er₂O₃. Compoziții similare au fost utilizate anterior pentru obținerea filmelor pentru aplicații ca ghiduri de undă, dar mecanismul de formare al fazelor prin tratamentul termic al gelurilor corespunzătoare nu a fost abordat anterior. Gelurile obținute prin gelifierea soluțiilor au fost analizate prin analiză termogravimetrică și termodiferențială (DTA / TGA) pentru a determina comportamentul lor termic și prin spectroscopie IR (FT-IR) și Microscopie Electronică de Baleaj (SEM) pentru a evalua structura si morfologia lor. Pe baza rezultatelor obținute, gelurile au fost tratate termic la 500°C și 900°C. Pulberile tratate termic au fost caracterizate prin SEM, FT-IR, difracție de raze X (XRD) și fotoluminiscentă (PL). Influenta semnificativă a Er^{3 +} asupra formării fazelor a fost stabilită în ambele sisteme studiate.

and thermal treatments, and can be doped with transition metal ions to obtain luminescent materials [3, 4].

In a previous study the Er³⁺ doped silicatitania or silica-titania-alumina films with the molar compositions of 90%SiO₂-10%TiO₂ or 85%SiO₂--10%TiO₂-5%Al₂O₃ and 0.5%Er₂O₃ were prepared by sol-gel method for waveguide applications [5]. It was established that the presence of Al³⁺ in the enhanced composition the homogeneous distribution of Er³⁺ in the samples' composition, but decreased the resulted films' chemical stability. In order to explain the mentioned behaviour a comparative phase formation study on the gels resulted from the solutions used for films deposition could be of interest.

Among the different technologies which are employed to develop materials suitable for photonics, sol–gel processing exhibits several

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Reagents pН Experimental Sample Molar ratio / Raport molar Probe Precursori conditions Condițiile experimentale ROH H_2O catalyst Er_2O_3 T (⁰C) t (h) \sum precursor $\overline{\sum}$ precursor Σ precursor \sum precursor ST Si(OC₂H₅)₄₊ 9.1 1.85 0.0174 3 50 3 -Ti(OC₂H₅)₄ Si(OC₂H₅)₄₊ 1.85 0.0174 3 91 0.5 50 3 ST-Er Ti(OC₂H₅)₄+ErCl₃ 1.85 0.0174 3 Si(OC₂H₅)₄₊ 19.3 3.5 50 -Ti(OC₂H₅)₄+ STA $AI(NO_3)_3$ Si(OC₂H₅)₄₊ 1.85 0.0174 19.3 0.5 3.5 50 3 Ti(OC₂H₅)₄₊ STA-Er AI(NO₃)_{3,}+ErCl₃

Composition of the starting solutions and the experimental conditions for gels preparation Compoziția soluțiilor inițiale și condițiile experimentale pentru prepararea gelurilor

R= - C₂H₅; 0.5 mol% Er₂O₃

advantages in terms of composition, rare-earth solubility, design, tailoring of optical properties as well as fabrication of films, waveguides, photonic crystals, and bulk glasses. The binary silica-based systems, such as silica–titania [6, 7], silica–hafnia [8], silica–alumina [9], silica-zirconia [10] and phosphosilicate [11] are of particular interest allowing the tailoring of the optical and spectroscopic properties [12].

In the present paper the sol-gel preparation of the nanostructured Er³-silica-titania and Er³silica-titania-alumina powders was approached and the mechanism of phase formation was investigated. The compositions were similar to those used previously for waveguide preparation.

2. Experimental

2.1. Gels and powders preparation

The experimental conditions used for obtaining the nanostructured oxide powders by solgel method were studied and are presented in Table 1. The selected compositions in the SiO₂-TiO₂ binary and SiO₂-TiO₂-Al₂O₃ ternary system, undoped and doped with Er_2O_3 were the following: 90%SiO₂-10%TiO₂ or 85%SiO₂-10%TiO₂-5%Al₂O₃ and 0.5 % Er_2O_3 . The compositions were selected based on the literature data and our previous works [13, 14].

As precursors the corresponding alkoxides: tetraethyl-ortosilicate (TEOS) (p.a., Merck, Darmstadt, Germany) as SiO₂ and tetraethyleortotitanate, Ti(O-C₂H₅)₄ (p.a., Merck, Darmstadt, Germany) as TiO₂ sources and salts: Al(NO₃)₃ (Aldrich) as Al₂O₃ source and ErCl₃ (Aldrich) as erbium source were used. The ethanol, C₂H₅OH (absolute, Merck, Darmstadt, Germany) was used as solvent, the nitric acid, HNO3 (65%, Merck, Darmstadt, Germany) as catalyst and the water for hydrolysis. The reaction was kept under stirring on water bath at 50°C for 3h. The solutions were kept at room temperature (40 days), to obtain gels. The

gels were thermally treated at 500 °C or 900 °C for 120 min, using a heating rate of 1 °C/min.

The resulting gels and powders, prepared from the solutions obtained were labeled as following: SiO_2 -TiO₂ (ST), SiO_2 -TiO₂-Al₂O₃ (STA), Er³⁺ doped SiO_2 -TiO₂ (ST-Er) and Er³⁺ doped SiO₂-TiO₂-Al₂O₃ (STA-Er), respectively.

2.2. Samples characterization

The morphology of the samples was investigated by **scanning electron microscopy** (SEM) using a high-resolution microscope, FEI Quanta 3D FEG model, operating at 15 kV, equipped with an energy dispersive X-ray (EDX) spectrometer Apollo X. The analyses were done in high vacuum mode, with Everhart–Thornley secondary electron detector.

Fourier-transform infrared (FT-IR) spectra were obtained using a Nicolet Spectrometer 6700 between 400 and 4000 cm⁻¹.

The **thermal behavior** of the synthetized gels was determined by differential thermal analysis and thermo-gravimetric analysis (TG/DTA) using Mettler-Toledo TGA/DTA 851° equipment in Al₂O₃ crucibles and in flowing air atmosphere. The maximum temperature was set at 900 °C and the heating rate was of 10 °C/min.

The structure of the powders was determined by **X-ray diffraction** (XRD) method. The asymmetrical reflection measurements were performed with an Ultima IV diffractometer (Rigaku Corp., Japan), using Cu K α radiation (λ = 1.5405 Å), operated at 30 mA and 40 kV.

The visible **photoluminescence** (PL) spectra were recorded with a Jasco FP-6500 Spectrofluorometer, with the Epifluorescence attachment - Jasco EFA-383, using 5 nm band passes for the excitation and the emission monochromators, the detector response of 1 sec, the scan rate of 100 nm/min and data pitch of 0.5 nm. The excitation wavelength was 355 nm.

Table1

A.Rusu, L. Predoană, S. Preda, J. Pandele Cusu, S. Petrescu, M. Zaharescu / Nanopulberi de SiO₂-TiO₂ sau SiO₂-TiO₂-Al₂O₃ dopate cu Erbiu preparate prin metoda sol-gel









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Fig. 1 - SEM images of the powders / Imaginile SEM ale pulberilor a) SiO₂-TiO₂, b) SiO₂-TiO₂-Al₂O₃, c) SiO₂-TiO₂-Er₂O₃ and d) SiO₂-TiO₂-Al₂O₃-Er₂O₃.

3. Results and discussion

3.1. Characterization of the as-prepared gels

As mentioned above (see Introduction) the studied gels were obtained from solutions used for preparation of films with optical properties. The resulted gels were amorphous as determined by XRD measurements (not presented here).

3.1.1. Scanning Electron Microscopy

The morphology of the as-prepared gels is presented in Figure 1 (a, b, c. d).

In all cases formation of homogeneous gel aggregates is observed. The Er³ + and Al³ + doped gels lead to more fragmented pieces due probably, to the formation of additional phases as the results of the reaction between the dopants and the base components.

3.1.2. Thermal behaviour

The thermal behavior of the as-prepared gels was investigated by TGA/DTA methods. The curves corresponding to the decomposition of obtained gels are presented in Figures 2a and b. It could be noticed that the thermal decomposition of the gels take place in two steps.

In the first step, the elimination of water takes place in the 20-150 °C temperature range accompanied by an endothermal effect.

In the second step (between 150-400 °C for all samples), the structural hydroxyls are eliminated and the organic residues are burnt out, without



rig. 2 - rig/DTG/DTA curves of the / Curbele / ro/DTG/DTA ale probelor a) SiO₂-TiO₂ and SiO₂-TiO₂-Al₂O₃,
b) SiO₂-TiO₂-Er₂O₃ and SiO₂-TiO₂-Al₂O₃-Er₂O₃ samples (heating rate 10 °C/min) / (viteza de încălzire 10°C/min).

Table 2

The assignment of the vibration bands in FT-IR spectra of the as-prepared gels in the undoped and Er-doped SiO₂-TiO₂ and SiO₂-TiO₂-Al₂O₃ systems / Atribuirea benzilor de vibrație în spectrele FT-IR ale gelurilor preparate în sistemele SiO₂-TiO₂ și

SIO ₂ - IIO ₂ -AI ₂ O ₃ nedopate și dopate cu Er									
	Samples	s / Probe		Assignment and vibration mode					
				Atribuirea benzilor de vibratie					
ST	ST-Er	STA	STA -Er	· · · · · · · · · · · · · · · · · · ·					
471	459	435	459	Si-O-Si					
585	587	561	561	Ti-O, Al-O, Ti-O-Al					
787	767	794	800	Si-O-Si symmetrical stretching in amorphous SiO ₂					
				Si-O-Si vibrație de întindere simetrică în SiO ₂ amorf					
946	946	946	946	Si-OH, stretching vibration					
				Si-OH, vibrații de întindere					
1074	1074	1074	1074	Si-O-Si asymmetric stretching in SiO ₂ amorphous Al-O-Al					
				Si-O-Si vibrație de întindere asimetrică în SiO ₂ amorf,					
				AI-O-AI					
1190	1190	1190	1190	Si-O-Si, LO mode asymmetrical stretching in SiO ₂ amorf					
				Si-O-Si, LO mod de vibrație de întindere asimetrică în					
				SiO ₂ amorf					
1389	1389	1389	1389	v NO ₃					
1638	1640	1641	1638	v _s (OH) in H ₂ O in water / v _s (OH) în H ₂ O					
2358	2358	2358	2358	CO ₃ ²⁻					
2865	2854	2842	2847	v _{as} (CH)					
2928	2928	2914	2913	v _{as} (CH ₃)					
3448	3441	3436	3430	v _{as} (OH) adsorbed water / v _{as} (OH) apa adsorbită					

specific effect on the DTA curves. This behavior indicating that the endothermic effects of the gels decomposition and the exothermal effects of burning out organic residues overlap and compensate each other. Over 400 °C a small weight loss around 1% can be observed for all gels.

There is no evidence of specific thermal effects corresponding to reactions between components.

3.1.3. FT-IR spectroscopy

The FT-IR spectra of the as-prepared gels are presented in Figure 3 and the assignment of the vibration bands are summarized in Table 2.

It can be noticed that the spectra are very similar with the spectra of the pure SiO_2 gels [15, 16], due to high amount of the SiO_2 in the samples.

Broad absorption bands in all gels between 3500 cm⁻¹ and 3200 cm⁻¹ were observed that indicate the presence of the hydroxyl groups and adsorbed water. The bands around 2850-2920 cm⁻¹ shows the presence of the organic residues.

The band at about 1389 cm⁻¹ is assigned to the NO^{3-} vibration, due to the presence in the reaction mixture of HNO_3 catalyst and of the $Al(NO_3)_3$ used as Al precursor. The band at about 1638 cm⁻¹ is assigned to the bending vibration of the molecular water.

The band around 1074 cm⁻¹ is attributed to Si-O-Si asymmetrical stretching in amorphous SiO₂. The 946 cm⁻¹ band indicates the presence of Si-OH, stretching vibration while the band about 459 cm^{-1} is attributed to Si-O-Si bonds.



Fig. 3 - FT-IR spectra of the as-prepared gels Spectrele FT-IR ale gelurilor.

3.1.4. Photoluminescence (PL) measurements

visible photoluminescence The (PL) spectrum of SiO₂-TiO₂-Er and SiO₂-TiO₂-Al₂O₃-Er gels are presented in Figure 4. In both cases at an excitation wavelenght of 355 nm, four emission bands centered at 389, 401, 468 and 533 nm were observed. These emission bands which correspond to Er³⁺ luminescence, are weak in the gel form and consist of several very broad superimposed bands. Thus, the emission band at 401 nm may appear from the radiative transitions from the level ²H_{9/2} to the ground level ⁴I_{15/2}. The emission bands at 468 and 533 nm are attributed to the radiative trasitions from the levels ${}^{2}H_{11/2} \rightarrow {}^{4}I_{15/2}$ and ${}^{4}S_{3/2} \rightarrow {}^{4}I_{15/2}$,

respectively. In the presence of Al³⁺, the intensity of the Er³⁺ luminescence decreases and the emission bands at 401 and 422 nm (${}^{2}H_{9/2} \rightarrow {}^{4}I_{15/2}$), remain well structured. Also, the emission band at 468 nm, attributed to ${}^{4}F_{5/2} \rightarrow {}^{4}I_{15/2}$ seems to be more intense and well structured as compared to that samples without Al³⁺.



Fig. 4 - Visible photoluminescence spectra of the Er³⁺-doped SiO₂-TiO₂ and SiO₂-TiO₂-Al₂O₃ gels / Spectrele de fotoluminiscenţă în vizibil ale gelurilor SiO₂-TiO₂ şi SiO₂-TiO₂-Al₂O₃ dopate cu Er³⁺.

Previously [5], in the case of Er^{3+} -doped SiO₂-TiO₂ films, it was observed that the e⁻ -hole pairs are generated in two photons transition in the electron subsystem of SiO₂-TiO₂, leading to a slow energy transfer to Er^{3+} . Thus, we may assume that in the case of gels, the energy transfer to Er^{3+} is very weak and the behavior may be attributed to the Er^{3+} photoluminescence in the SiO₂ based structures and/or to the presence of the impurities in the silica matrix (structural OH, adsorbed CO₂ or H₂O) dopate with Er^3 .





Table 3

The assignment of the vibration bands in FT-IR spectra of the thermally treated samples in the undoped and Er-doped SiO₂-TiO₂ and SiO₂-TiO₂-Al₂O₃ systems / Atribuirea benzilor de vibrație în spectrele FT-IR ale pulberilor tratate termic în sistemele SiO₂-TiO₂ si SiO₂-TiO₂-Al₂O₃ nedopate si dopate cu Er

Samples Assignment and vibration mode Atribuirea benzilor de vibrație ST ST-Er STA STA-Er ST ST-Er STA STA-Er ST ST-Er STA STA-Er STA STA-Er STA STA-Er STA STA STA-Er 453 453 453 453 465 465 465 465 Si-O-Si Si-O-Si Si-O-Si Si-O-Si Si-O-Si Si-O-Si Si-O-Si SiO2				•	0202		• 2 / 2 • 3	nea optate .	
500° C 900° C Atribuirea benzilor de vibrație ST ST-Er STA STA-Er ST ST-Er STA STA-Er STA STA STA-Er STA STA-Er STA STA-Er STA STA-Er STA Sta <td></td> <td></td> <td></td> <td>Sam</td> <td>Assignment and vibration mode</td>				Sam	Assignment and vibration mode				
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Image: Second system Image: Se									Si-O-Si, LO mod de vibrație de întindere
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2410 2410 2410 2360 2365 2365 CO ₃ ²⁻ 2850 2850 2850 2850 2848 2850 2848 2850 v(CH) 2914 2914 2914 2914 2928 2928 2928 v _{as} (CH ₃) 3444 3447 3444 3442 3456 3444 v _{as} (OH) adsorbed water / apa adsorbită	1636	1636	1636	1636	1638	1638	1638	1638	v₅(OH) in water <i>/ în apă</i>
2850 2850 2850 2848 2850 2848 2850 v(CH) 2914 2914 2914 2914 2928 2928 2928 2928 v _{as} (CH ₃) 3444 3447 3444 3444 3442 3456 3444 v _{as} (OH) adsorbed water / apa adsorbită	2410	2410	2410	2410	2360	2365	2360	2365	CO ₃ ²⁻
2914 2914 2914 2928 2928 2928 2928 vas(CH ₃) 3444 3447 3444 3447 3444 3442 3456 3444 vas(OH) adsorbed water / apa adsorbită	2850	2850	2850	2850	2848	2850	2848	2850	v(CH)
3444 3447 3444 3447 3444 3442 3456 3444 v _{as} (OH) adsorbed water / apa adsorbită	2914	2914	2914	2914	2928	2928	2928	2928	v _{as} (CH ₃)
	3444	3447	3444	3447	3444	3442	3456	3444	vas (OH) adsorbed water / apa adsorbită

h

3.2. Thermally treated samples

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Based on the results of thermal analysis the synthesized gels were thermally treated at 500 and 900 $^{\circ}$ C for 2 h.

3.2.1. Scanning Electron Microscopy

The SEM images of the thermally treated samples are presented in the Figure 5.

In all cases the formation of homogeneous gel aggregates is observed. No significant modification of the morphology of the gels thermally treated at 500 and 900 °C is observed.

3.2.2. FT-IR spectroscopy

The FT-IR spectra of the thermally treated powders are presented in Figure 6 and the assignment of the vibration bands is summarized in Table 3.

As compared with the as-prepared gels, the intensities of the vibration bands assigned to the hydroxyl groups, adsorbed water, NO_{3^-} , decreased for all thermally treated samples.

The vibration band of metal oxygen bonds at about 450 cm⁻¹ increases, indicating their better structuring. In the same time the vibration band at about 935 cm⁻¹ decreases. The decreasing of the mentioned band is explained by the polycondensation reactions that occur between the -Si-OH structural units or between the Si-OH and Al-OH ones, leading to the formation of Si-O-Si or Si-O-Al bonds.

An interesting result is observed in the case of the Er^{3+} doped samples for which the mentioned vibration band practically vanished starting with the thermal treatment at 500 °C. It could be concluded that the presence of Er^{3+} enhanced the mentioned polycondensation reactions.

3.2.3. X-ray diffraction measurements

Based on the TGA/DTA results, the samples were thermally treated at 500 °C and 900 °C for 2 h.

The X-ray diffraction patterns of the powders are presented in the Figure 7.

According to the results presented in the Figure 7, the powders without Er^{3+} are amorphous at those temperature, but the presence of the Er^{3+} in the samples determines a very low crystallization of anatase phase as identified with ICDD file no. 00-021-1272.

The influence of SiO₂ matrix on the crystallization behavior of titanium dioxide is well-documented [17]. According to Best et al. [18], TiO₂ and SiO₂ are immiscible and any crystallization in the mixed system implies segregation or diffusion of Ti. Sankur et al. [19] reported that the segregation phenomenon of Ti is driven by the initial composition of the mixture, as well as crystallization temperature and the crystal



Fig. 6 - FT-IR spectra of the powders resulted by gels thermal treatment at a) 500 °C and b) 900 °C / Spectrele FT-IR ale pulberilor rezultate din tratamentul termic al gelurilor la a) 500 °C şi b) 900°C.

size. Chao et al. [20] reported that the addition of SiO₂ into TiO₂ matrix retards crystallization of the TiO₂. It was also noted that an increasing of the SiO₂ content resulted in a decreasing particle size, confirmed by the XRD analysis taken after annealing the samples at 500 °C and 900 °C. Machida et al. [21] reported the presence of amorphous SiO₂ around TiO₂, which would prevent the growth of TiO₂ particles. Klein et al. [22] reported that the Si-excess in SiO₂-TiO₂ systems remained in amorphous state up to 900 °C.

In crystallization, the most important parameter is the critical nucleus size. Around this value, there is a competition between the formation of new crystalline phase and the clusters dissolution. In the investigated systems, the SiO₂ matrix may prevent the clustering of oxide particles (TiO₂ and Al₂O₃) to form nuclei and reach the critical size, and, hence, crystal growth, which easily explain the amorphous state up to 900 °C of SiO₂-TiO₂ and SiO₂-TiO₂-Al₂O₃ systems, for the given compositions. In the same time, at low loadings, the small size of crystals

A.Rusu, L. Predoană, S. Preda, J. Pandele Cusu, S. Petrescu, M. Zaharescu / Nanopulberi de SiO₂-TiO₂ sau SiO₂-TiO₂-Al₂O₃ dopate cu Erbiu preparate prin metoda sol-gel



Fig. 7 - X-ray diffraction patterns of the thermally treated powders / Difractogramele pulberilor tratatate termic.



Fig. 8 - Visible photoluminescence spectra of the Er³⁺-doped SiO₂-TiO₂ and SiO₂-TiO₂-Al₂O₃ powders thermally treated at 500 °C / *Spectrele de fotoluminiscența în vizibil ale pulberilor SiO₂-TiO₂ și SiO₂-TiO₂-Al₂O₃ dopate cu Er³⁺ tratate termic la 500 °C.*

and high dispersion in the amorphous SiO_2 matrix causes significant line broadening in X-ray diffraction (XRD) powder patterns. Hence, the absence of lines from the crystalline phase in an XRD pattern does not necessarily rule out the presence of small particles of the crystalline oxide [23].

A different behavior it was noticed for Er^{3+} doped systems. Both systems (SiO₂-TiO₂ and SiO₂-TiO₂-Al₂O₃) present a crystalline phase, which was identified as TiO₂, anatase. The competition between Er^{3+} ion clustering, which may act as crystal seeds for anatase crystal growth and SiO₂ matrix constraints is favorable to the crystallization of anatase phase.

3.2.4. Photoluminescence (PL) measurements

The visible photoluminescence (PL) spectra of the as-prepared gels and thermally treated samples at 500 °C, are presented in the Figure 8. It could be noticed that for both SiO₂-TiO₂ and SiO₂-TiO₂-Al₂O₃ systems, no significant changes between as-prepared gels and thermally treated samples was observed. As mentioned in the case of the gels, the very low energetic transfer

Er³⁺ to could assigned to the be Er³⁺ photoluminescence of in SiO₂ based structures and/or to the presence of some impurities in the silica matrix (structural OH, adsorbed CO₂ or H₂O) dopate with Er³. The same aspects were observed also for the thermally treated samples leading to the conclusion that the residual impurities noticed stil in the case of thermally treated samples determine their low photoluminescence.

To bring more information on the matter the studies will be continued on samples thermally treated at 900°C and using a higher excitation wave, in the 950-1200 nm.

4. Conclusions

Gels and nanostructured powders were obtained by sol-gel method in the Er^{3+} -doped SiO₂--TiO₂ and SiO₂-TiO₂-Al₂O₃ systems.

The as-prepared gels that contain mainly SiO_2 in their composition present similar FT-IR spectra to that of pure SiO_2 . The presence of the additives is put in evidence only by small displacements of the Si-O-Si and Si-OH characteristic vibration bands.

In the case of the thermally treated samples at 500 and 900 °C, FT-IR spectroscopy show the better structuring of M-O-M bonds, while significantly reducing the vibration bands of organic components, adsorbed water and structural hydroxyls.

An interesting behavior is observed in the case of Er^{3+} doped samples that shows its influence in enhancing the polycondensation of the Si-OH and Al-OH structural units.

The XRD measurements show an amorphous character of all un-doped samples after thermal treatment at both used temperatures (500 and 900 °C) while in the case of Er^{3+} doped samples the crystallization of TiO₂ anatase phase crystallization was notice.

The Er³⁺ photoluminescence in gels and nanostructured powders is very weak due probably of the presence of the organic components, adsorbed water, and structural hydroxyls in their composition that could quench the fluorescence.

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